Bipolar Transistor

(–)50 V, (–)3 A, Low $V_{CE}(sat)$ (PNP)NPN Single TP/TP-FA

Features

- Adoption of FBET and MBIT Processes
- Large Current Capacitance and Wide ASO
- Low Collector to Emitter Saturation Voltage
- Fast Switching Speed
- Small and Slim Package Making it Easy to Make 2SB1202/2SD1802-used Sets Smaller
- These Devices are Pb-Free and are RoHS Compliant

Applications

• Voltage Regulators, Relay Drivers, Lamp Drivers, Electrical Equipment

ABSOLUTE MAXIMUM RATINGS at $T_A = 25^{\circ}C$

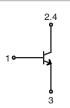
| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|------------------|-----------------------|-----------------|------|
| Collector to Base Voltage | V _{CBO} | | (-)60 | ٧ |
| Collector to Emitter Voltage | V _{CEO} | | (-)50 | V |
| Emitter to Base Voltage | V _{EBO} | | (-)6 | V |
| Collector Current | I _C | | (-)3 | Α |
| Collector Current (Pulse) | I _{CP} | | (-)6 | Α |
| Collector Dissipation | P _C | | 1 | W |
| | | T _C = 25°C | 15 | W |
| Junction Temperature | TJ | | 150 | ∘C |
| Storage Temperature | T _{STG} | | – 55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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(For PNP, the polarity is reversed.)

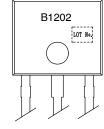


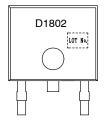


IPAK / TP CASE 369AJ

DPAK / TP-FA CASE 369AH

MARKING DIAGRAM





ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

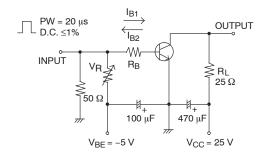
| | | | Ratings | | | |
|---|-----------------------|---|---------|-------------|-----------|------|
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
| Collector Cutoff Current | I _{CBO} | V _{CB} = (-)40 V, I _E = 0 A | | | (-)1 | μΑ |
| Emitter Cutoff Current I_{EBO} $V_{EB} = (-1)^{-1}$ | | V _{EB} = (-)4V, I _C = 0 A | | | (-)1 | μΑ |
| DC Current Gain | h _{FE} 1 | V _{CE} = (-)2 V, I _C = (-)100 mA | 100* | | 560* | |
| | h _{FE} 2 | V _{CE} = (-)2 V, I _C = (-)3 A | 35 | | | |
| Gain-Bandwidth Product | f _T | V _{CE} = (-)10 V, I _C = (-)50 mA | | | | MHz |
| Output Capacitance | Cob | V _{CB} = (-)10 V, f = 1 MHz | | (39)25 | | pF |
| Collector to Emitter Saturation Voltage | V _{CE} (sat) | I _C = (-)2 A, I _B = (-)100 mA | | (-0.35)0.19 | (-0.7)0.5 | V |
| Base to Emitter Saturation Voltage | V _{BE} (sat) | V _{CE} = (-)2 V, I _C = (-)100 mA | | (-)0.94 | (-)1.2 | V |
| Collector to Base Breakdown Voltage | V _{(BR)CBO} | I _C = (-)10 μA, I _E = 0 A | (-)60 | | | ٧ |
| Collector to Emitter Breakdown Voltage | V _{(BR)CEO} | I_C = (-)1 mA, R_{BE} = Ω | (-)50 | | | V |
| Emitter to Base Breakdown Voltage | V _{(BR)EBO} | I _E = (-)10 μA, I _C = 0 A | (-)6 | | | V |
| Turn-On Time | ton | See specified Test Circuit | | 70 | | ns |
| Storage Time | tstg | Gircuit | | (450)650 | | ns |
| Fall Time | tf | 1 | | 35 | | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*The 2SB1202/2SD1802 are classified by 100 mA h_{FE} as follows:

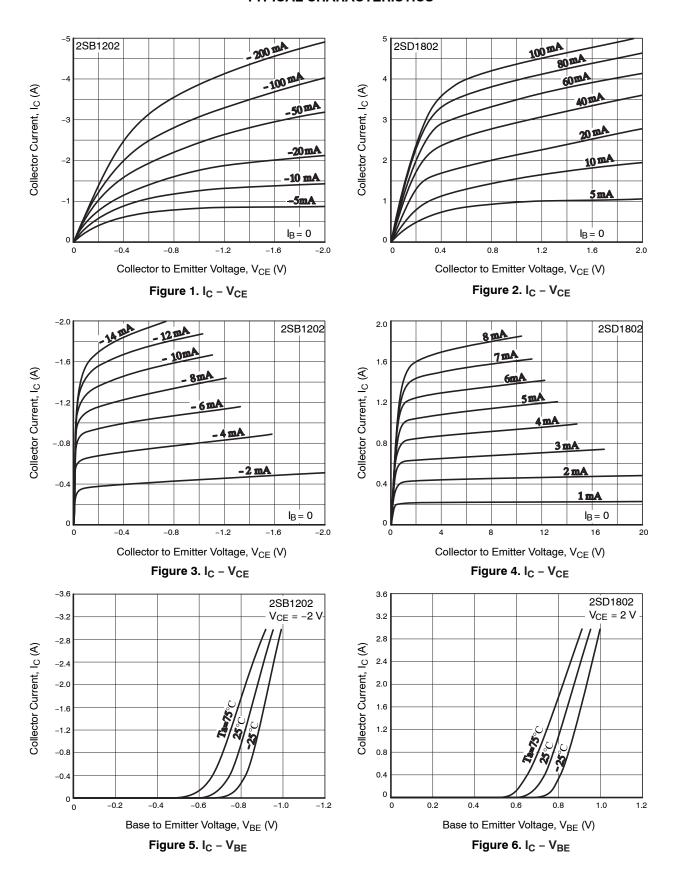
| Rank | R | S | Т | U |
|-----------------|------------|------------|------------|------------|
| h _{FE} | 100 to 200 | 140 to 280 | 200 to 400 | 280 to 560 |

Switching Time Test Circuit

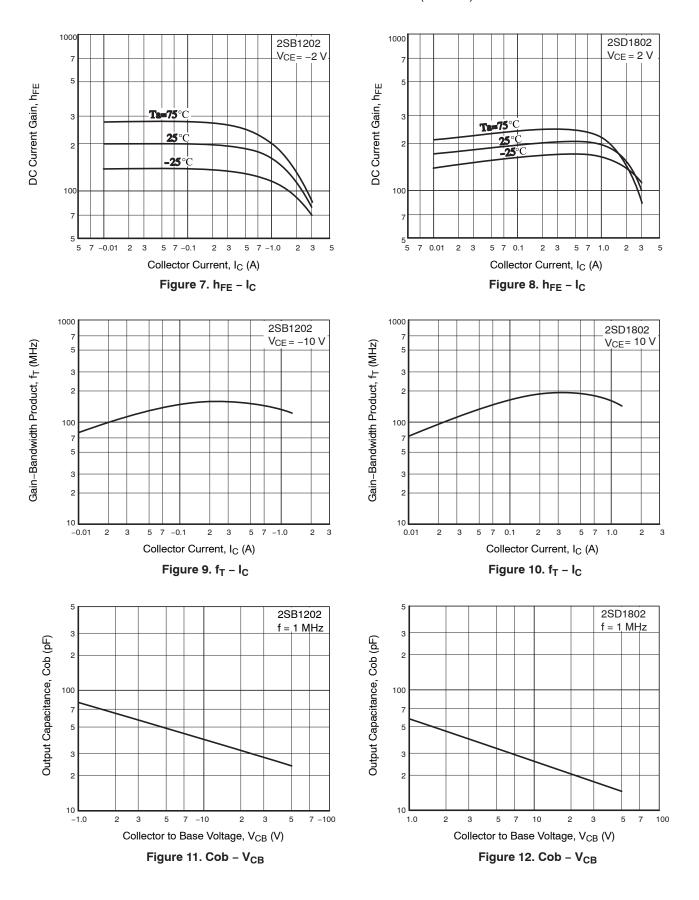


 I_C = 10 I_{B1} = -10 I_{B2} = 1 A For PNP, the polarity is reversed.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (continued)



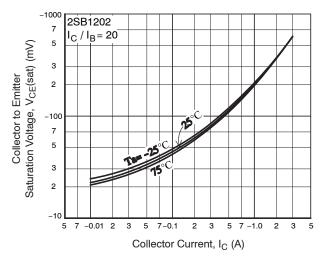


Figure 13. V_{CE}(sat) - I_C

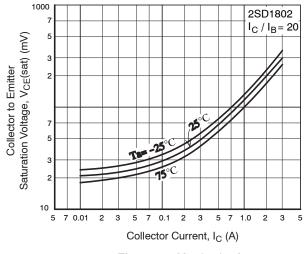


Figure 14. V_{CE}(sat) - I_C

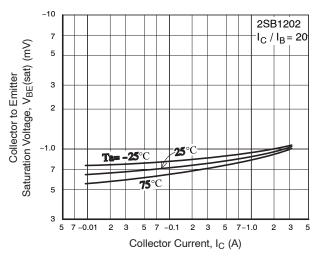


Figure 15. V_{BE}(sat) - I_C

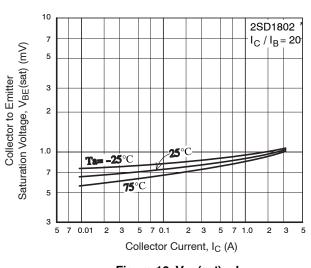


Figure 16. $V_{BE}(sat) - I_{C}$

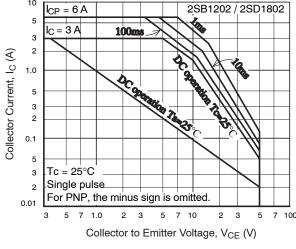


Figure 17. ASO

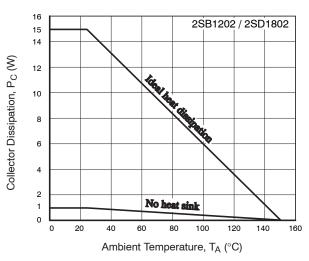


Figure 18. P_C – T_A

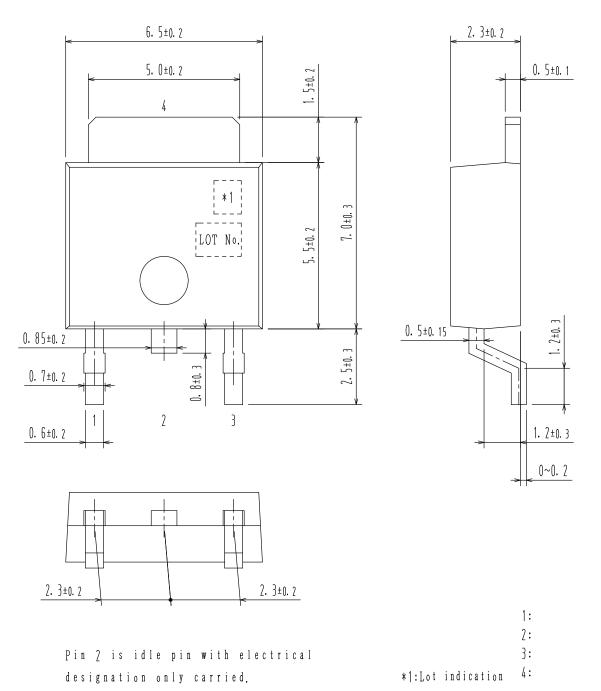
ORDERING INFORMATION

| Device | Package | Shipping† | memo |
|---------------|---------|--------------|---------|
| 2SB1202S-E | TP | 500pcs./bag | Pb-Free |
| 2SB1202T-E | TP | 500pcs./bag | |
| 2SD1802S-E | TP | 500pcs./bag | |
| 2SD1802T-E | TP | 500pcs./bag | |
| 2SB1202S-TL-E | TP-FA | 700pcs./reel | |
| 2SB1202T-TL-E | TP-FA | 700pcs./reel | |
| 2SD1802S-TL-E | TP-FA | 700pcs./reel | |
| 2SD1802T-TL-E | TP-FA | 700pcs./reel | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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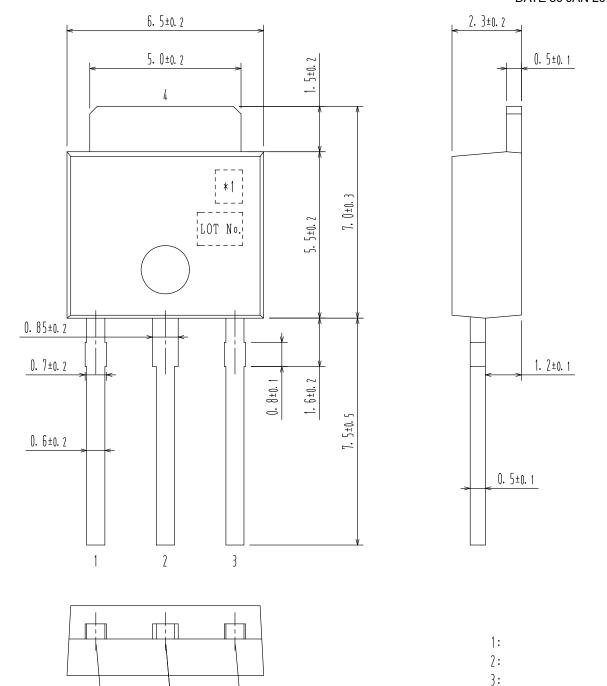
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*1:Lot indication

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